

**FEATURES**

- Small Footprint
- Low Capacitance
- High Speed

**DESCRIPTION**

The **SD019-111-411** is a silicon photodiode assembled in a 0805 SMT package.

**APPLICATIONS**

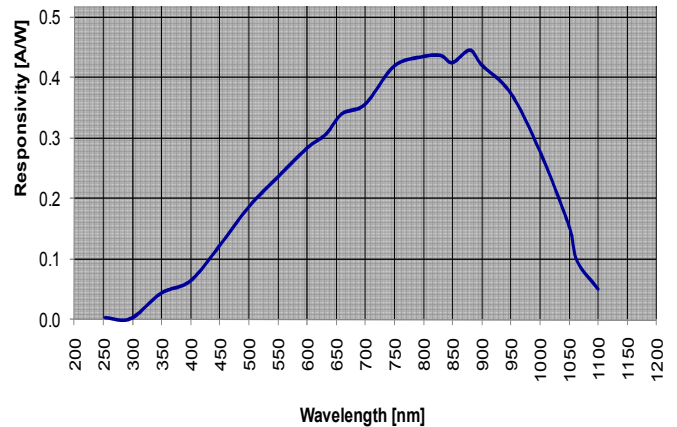
- Industrial Sensors
- Light Management
- Handheld Devices

**ABSOLUTE MAXIMUM RATING**

T<sub>a</sub> = 25°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V <sub>R</sub>	Reverse Voltage		50	V
T <sub>Op</sub>	Operating Temperature	-40	+105	°C
T <sub>Stg</sub>	Storage Temperature	-50	+125	°C
T <sub>S</sub>	Soldering Temperature*		+260	°C

**TYPICAL SPECTRAL RESPONSE**



**ELECTRO-OPTICAL CHARACTERISTICS RATING**

T<sub>a</sub> = 25°C, UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V <sub>f</sub>	Forward Voltage	I <sub>f</sub> = 10 mA	0.5	0.8	1.3	V
I <sub>L</sub>	Light Current (2856K)	V <sub>R</sub> = 5V; H = 1000 lux	-	3.2	-	μA
V <sub>br</sub>	Breakdown Voltage	I <sub>R</sub> = 100 μA	50	-	-	V
R <sub>sh</sub>	Shunt Resistance	V <sub>bias</sub> = 10 mV	-	2.0	-	GΩ
I <sub>d</sub>	Dark Current	V <sub>R</sub> = 10 V	-	-	0.5	nA
C <sub>j</sub>	Junction Capacitance	V <sub>R</sub> = 5V; f = 1000 kHz	-	6.0	-	pF
t <sub>r</sub>	Rise Time	V <sub>R</sub> = 3V; R <sub>i</sub> = 1000Ω	-	1	-	μS

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